

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Chen et al.

FAX RECEIVED

Serial No.: 09/748,256

Group Art Unit: 2811

MAR 28 2003

Filed: December 27, 2000

Examiner: Ori Nadav

TECHNOLOGY CENTER 2800

For: METHOD FOR FABRICATING COMPLEMENTARY METAL OXIDE
SEMICONDUCTOR (CMOS) DEVICES ON A MIXED BULK AND SILICON-ON-
INSULATOR (SOI) SUBSTRATE

Honorable Commissioner of Patents
Washington, D.C. 20231
Box AF

AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the Office Action dated January 28, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:**Please amend the claims to read as follows:**

- do not
entirely
on
29. (Thrice Amended) A semiconductor device comprising:
a bulk silicon region comprising single crystal silicon; and
a silicon-on-insulator (SOI) region comprising:
an insulator layer which is formed beneath an upper portion of said single crystal silicon and has at least one lateral end portion adjacent to a lower portion of said single crystal silicon; and
at least one isolation oxide formed in said upper portion of said single crystal silicon so as to form at least one island of said single crystal silicon on an upper surface of said insulator layer,
wherein said upper portion of said single crystal silicon and said lower portion of said single crystal silicon have a same crystal orientation, and
wherein said upper portion of said single crystal silicon comprises crystallized epitaxial silicon which is grown from said lower portion of said single crystal silicon.